

Schottky Diode

Common Cathode

Part number

Very low Vf

• low Irm values

protection circuits Low noise switching

DSB 20 I 15 PA

Features / Advantages:

• Extremely low switching losses

• Improved thermal behaviour

 High reliability circuit operation Low voltage peaks for reduced

High Performance Schottky Diode

Low Loss and Soft Recovery

DSB 20 | 15 PA

advanced

V _{RRM} =	15 V
I _{FAV} =	20 A
V _F =	0.39 V

Backside: cathode

Unit

V

μA

mΑ

V

V

÷

15

10

40

0.48

0.60

max.

Package:

- Housing: TO-220
- Industry standard outline
- Epoxy meets UL 94V-0

Ratings

typ.

• RoHS compliant

min.

3()

Applications:

- Rectifiers in switch mode power supplies (SMPS)
- converters
- - Free wheeling diode in low voltage

Conditions Symbol Definition V_{RRM} $T_{VJ} = 25^{\circ}C$ max. repetitive reverse voltage reverse current $T_{VJ} = 25^{\circ}C$ I_R V_R = 15 V V_R = $T_{vJ} = 100^{\circ}C$ 15V \overline{V}_{F} forward voltage $T_{VJ} = 25^{\circ}C$ I_F = 20 A 40 A I_{F} = 20 A т

		$I_F = 20 A$	T _{vJ} = 125°C			0.39	V
		$I_F = 40 A$				0.54	V
IFAV	average forward current	rectangular, d = 0.5	$T_{c} = 130^{\circ}C$			20	A
V _{F0}	threshold voltage		T _{vJ} = 150°C			0.23	V
r _F	slope resistance } for power loss	calculation only				7.2	mΩ
R_{thJC}	thermal resistance junction to case					1.75	K/W
T _{vj}	virtual junction temperature			-55		150	°C
P _{tot}	total power dissipation		$T_c = 25^{\circ}C$			70	W
	max. forward surge current	t = 10 ms (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			160	Α
C	junction capacitance	V_R = tbdV; f = 1 MHz	$T_{vJ} = 25^{\circ}C$		tbd		pF

IXYS reserves the right to change limits, conditions and dimensions.

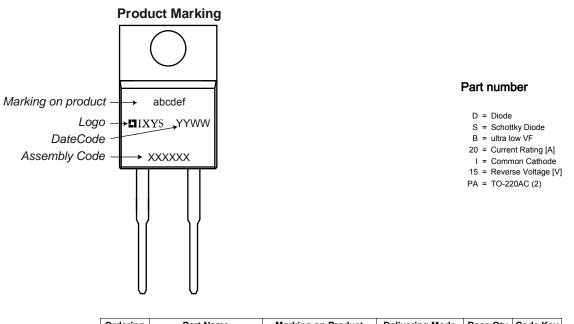




advanced

			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
IRMS	RMS current	per pin ¹⁾			35	Α
R _{thCH}	thermal resistance case to he	eatsink		0.50		K/W
T _{stg}	storage temperature		-55		150	°C
Weight				2		g
M _D	mounting torque		0.4		0.8	Nm
F _c	mounting force with clip		20		60	Ν

¹⁾ I_{RMS} is typically limited by: 1. pin-to-chip resistance; or by 2. current capability of the chip. In case of 1, a common cathode/anode configuration and a non-isolated backside, the whole current capability can be used by connecting the backside.



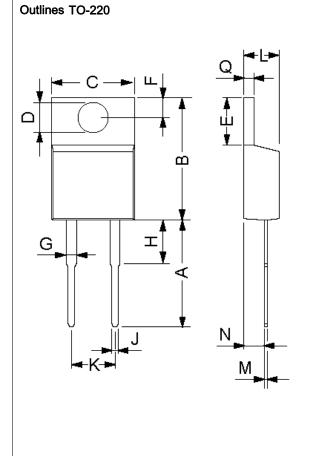
Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty Code Key
Standard	DSB 20 I 15 PA	DSB20I15PA	Tube	

Package				

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Dim.	Millimeter		Inches	
Dim.	Min.	Max.	Min.	Max.
А	12.7	14.73	0.5	0.58
В	14.23	16.51	0.56	0.65
C	9.66	10.66	0.38	0.42
D	3.54	4.08	0.139	0.161
Е	5.85	6.85	2.3	0.42
F	2.54	3.42	0.1	0.135
G	1.15	1.77	0.045	0.07
Н	-	6.35	-	0.25
J	0.64	0.89	0.025	0.035
К	4.83	5.33	0.19	0.21
L	3.56	4.82	0.14	0.19
М	0.51	0.76	0.02	0.03
Ν	2.04	2.49	0.08	0.115
Q	0.64	1.39	0.025	0.055

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